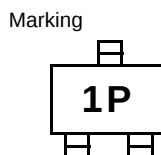
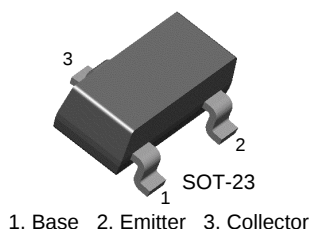


KST2222A

NPN Epitaxial Silicon Transistor

General Purpose Transistor



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	600	mA
P_C	Collector Power Dissipation	350	mW
T_{STG}	Storage Temperature Range	-55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}$, $I_E = 0$	75		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$, $I_B = 0$	40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}$, $I_C = 0$	6		V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 60\text{V}$, $I_E = 0$		0.01	μA
h_{FE}	DC Current Gain *	$V_{CE} = 10\text{V}$, $I_C = 0.1\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 1\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 10\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 150\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 500\text{mA}$	35 50 75 100 40	300	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage *	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$		0.3 1.0	V V
$V_{BE}(\text{sat})$	Base-Emitter Saturation Voltage *	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$	0.6	1.2 2.0	V V
f_T	Current Gain Bandwidth Product	$I_C = 20\text{mA}$, $V_{CE} = 20\text{V}$, $f = 100\text{MHz}$	300		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		8	pF
NF	Noise Figure	$I_C = 100\mu\text{A}$, $V_{CE} = 10\text{V}$ $R_S = 1\text{K}\Omega$, $f = 1\text{MHz}$		4	dB
t_{ON}	Turn On Time	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$ $V_{BE} = 0.5\text{V}$, $I_{B1} = 15\text{mA}$		35	ns
t_{OFF}	Turn Off Time	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$, $I_{B1} = I_{B2} = 15\text{mA}$		285	ns

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1. DC Current Gain

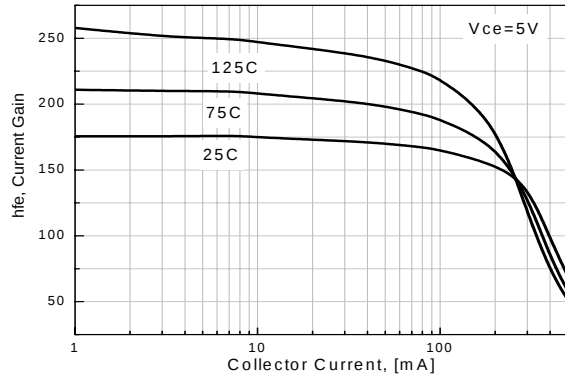


Figure 2. Collector-Emitter Saturation Voltage

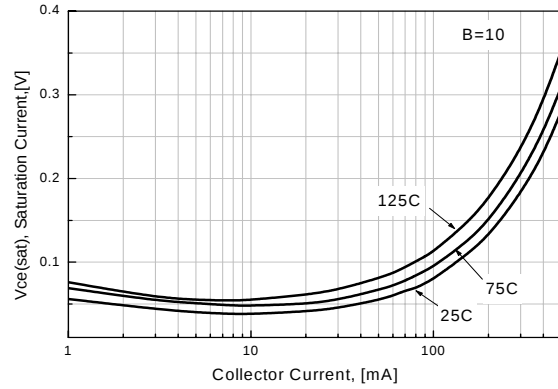


Figure 3. Base-Emitter Saturation Voltage

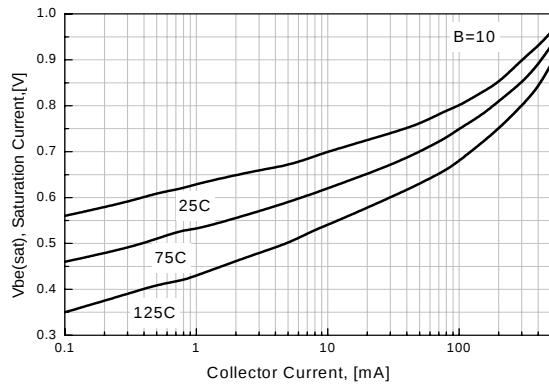


Figure 4. Collector - Base Leakage Current

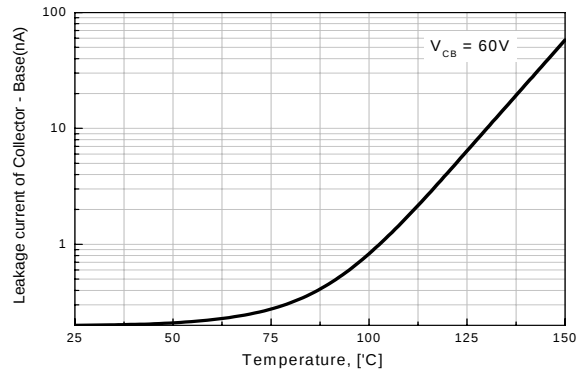


Figure 5. Output Capacitance

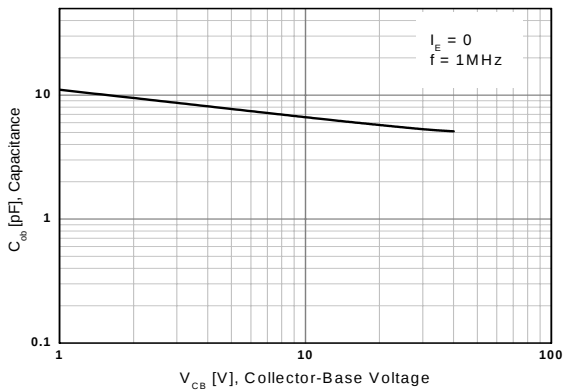
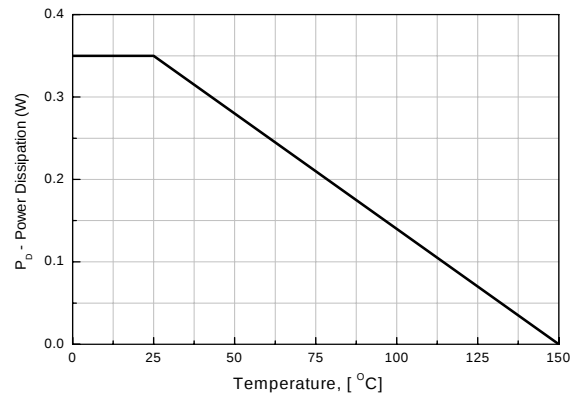
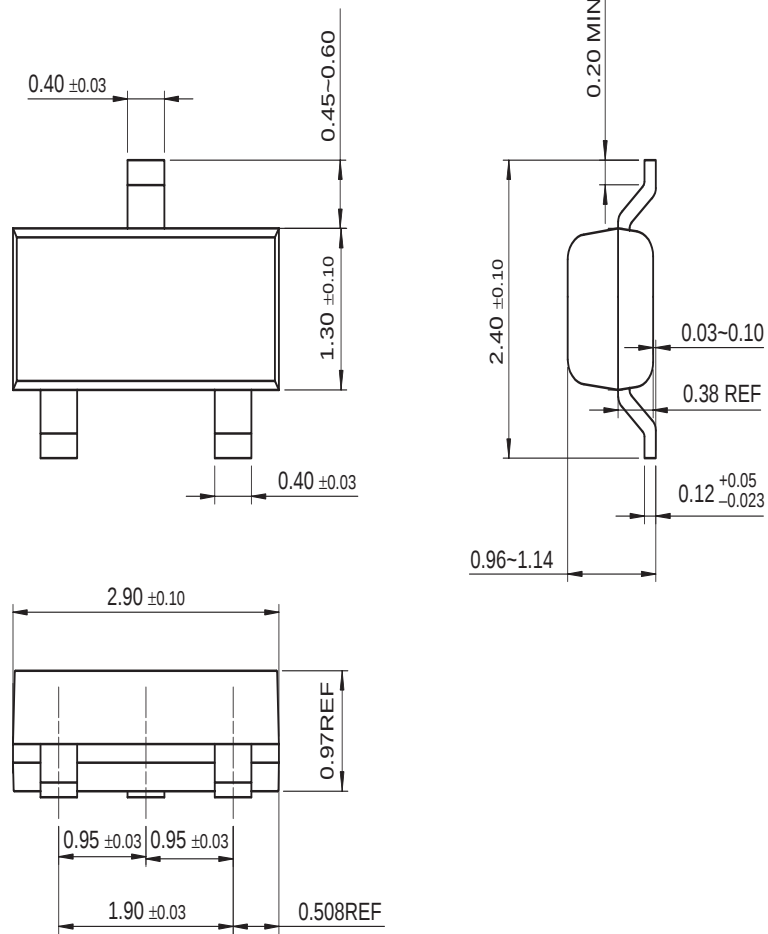


Figure 6. Power Dissipation vs Ambient Temperature



Mechanical Dimensions

SOT-23



Dimensions in Millimeters

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